SN74CBTLV3857
LOW-VOLTAGE 10-BIT FET BUS SWITCH
WITH INTERNAL PULLDOWN RESISTORS

- **Enable Signal Is SSTL_2 Compatible**
- **Flow-Through Architecture Optimizes PCB Layout**
- **Designed for Use With 200 Mbit/s Double Data-Rate (DDR) SDRAM Applications**
- **Switch On-State Resistance Is Designed to Eliminate Series Resistor to DDR SDRAM**
- **Internal 10-kΩ Pulldown Resistors to Ground on B Port**
- **Internal 50-kΩ Pullup Resistor on Output-Enable Input**
- **Rail-to-Rail Switching on Data I/O Ports**
- **I$_{off}$ Supports Partial-Power-Down Mode Operation**
- **Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II**

DBQ, DGV, DW, OR PW PACKAGE
(TOP VIEW)

V$_{REF}$	1	24	V$_{CC}$
A1	2	23	$\overline{OE}$
A2	3	22	B1
A3	4	21	B2
A4	5	20	B3
A5	6	19	B4
A6	7	18	B5
A7	8	17	B6
A8	9	16	B7
A9	10	15	B8
A10	11	14	B9
GND	12	13	B10
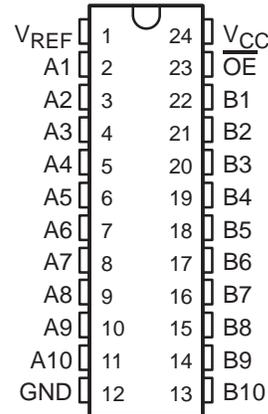
description/ordering information

This 10-bit FET bus switch is designed for 3-V to 3.6-V V$_{CC}$ operation and SSTL_2 output-enable ($\overline{OE}$) input levels.

When $\overline{OE}$ is low, the 10-bit bus switch is on, and port A is connected to port B. When $\overline{OE}$ is high, the switch is open, and the high-impedance state exists between the two ports. There are 10-kΩ pulldown resistors to ground on the B port.

The FET switch on-state resistance is designed to replace the series terminating resistor in the SSTL_2 data path.

This device is fully specified for partial-power-down applications using I$_{off}$. The I$_{off}$ feature ensures that damaging current will not backflow through the device when it is powered down. The device has isolation during power off.

ORDERING INFORMATION

T$_A$	PACKAGE†		ORDERABLE PART NUMBER	TOP-SIDE MARKING
−40°C to 85°C	QSOP – DBQ	Tape and reel	SN74CBTLV3857DBQR	CL857
	SOIC – DW	Tube	SN74CBTLV3857DW	CBTLV3857
		Tape and reel	SN74CBTLV3857DWR	
	TSSOP – PW	Tape and reel	SN74CBTLV3857PWR	CL857
	TVSOP – DGV	Tape and reel	SN74CBTLV3857DGVR	CL857

† Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.

FUNCTION TABLE

INPUT $\overline{OE}$	FUNCTION
L	A port = B port
H	Disconnect

Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

TEXAS INSTRUMENTS

logic diagram (positive logic)
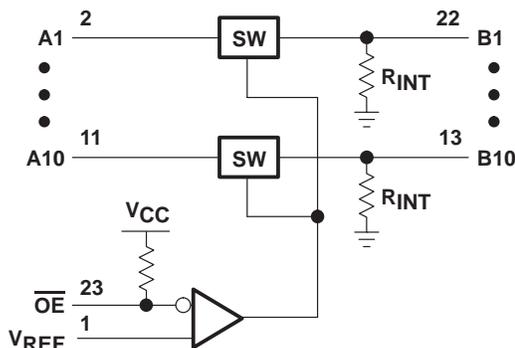
simplified schematic, each FET switch
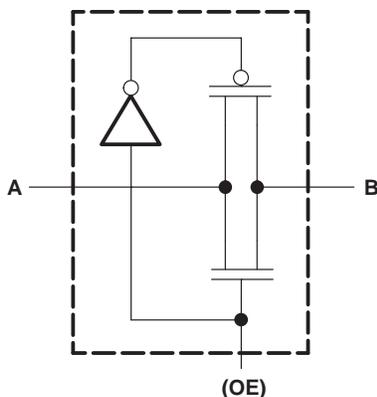
absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} .... –0.5 V to 4.6 V
Input voltage range ($\overline{OE}$ only), V_I (see Note 1) .... –0.5 V to V_{CC} + 0.5 V
Input voltage range (except $\overline{OE}$), V_I (see Note 1) .... –0.5 V to 4.6 V
Continuous channel current .... 48 mA
Input clamp current, I_{IK} ($V_{I/O} < 0$) .... –50 mA
Package thermal impedance, θ_{JA} (see Note 2): DBQ package .... 61°C/W
DGV package .... 86°C/W
DW package .... 46°C/W
PW package .... 88°C/W
Storage temperature range, T_{stg} .... –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and
   functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not
   implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
NOTES: 1.   The input and output negative-voltage ratings may be exceeded if the input and output current ratings are observed.
            2.   The package thermal impedance is calculated in accordance with JESD 51-7.

recommended operating conditions (see Note 3)

		MIN	NOM	MAX	UNIT
V_{CC}	Supply voltage	3	3.3	3.6	V
V_{REF}	Reference voltage ($0.38 \times V_{CC}$)	1.15	1.25	1.35	V
V_{IH}	AC high-level control input voltage	V_{REF} + 350 mV			V
V_{IL}	AC low-level control input voltage			V_{REF} – 350 mV	V
V_{IH}	DC high-level control input voltage	V_{REF} + 180 mV			V
V_{IL}	DC low-level control input voltage			V_{REF} – 180 mV	V
T_A	Operating free-air temperature	–40		85	°C

NOTE 3:   All unused control inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS			MIN	TYP†	MAX	UNIT
V_{IK}		V_{CC} = 3 V,	I_I = –18 mA				–1.2	V
I_I	$\overline{OE}$	V_{CC} = 3.6 V,	V_I = V_{CC} or GND				±1	mA
	A port						±5	µA
	B port						±1	mA
	V_{REF}						±5	µA
I_{CC}		V_{CC} = 3.6 V,	I_O = 0,	V_I = V_{CC} or GND			25	mA
C_i	Control inputs	V_I = 3 V or 0				3.5		pF
$C_{io(OFF)}$		V_O = 3 V or 0,	$\overline{OE}$ = V_{CC}			5		pF
r_{on}‡		V_{CC} = 3 V	V_I = 0,	I_I = 24 mA		5	8	Ω
			V_I = 0.9 V,	I_I = 24 mA		6	11	
			V_I = 1.25 V,	I_I = 24 mA		7	13	
			V_I = 1.6 V,	I_I = 24 mA		9	40	
r_{off}‡		V_{CC} = 0			1			MΩ
		V_{CC} = 3 V to 3.6 V,	V_I = 1.65 V,	$\overline{OE}$ = V_{CC}	1			

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ Measured by the voltage drop between the A and B terminals at the indicated current through the switch. Resistance is determined by the lower of the voltages of the two (A or B) terminals.

switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	
t_{pd}§	A or B	B or A		0.25	ns
t_{en}	$\overline{OE}$	A or B	1.4	4.2	ns
t_{dis}	$\overline{OE}$	A or B	1.4	4.8	ns

§ The propagation delay is the calculated RC time constant of the typical on-state resistance of the switch and the specified load capacitance, when driven by an ideal voltage source (zero output impedance).
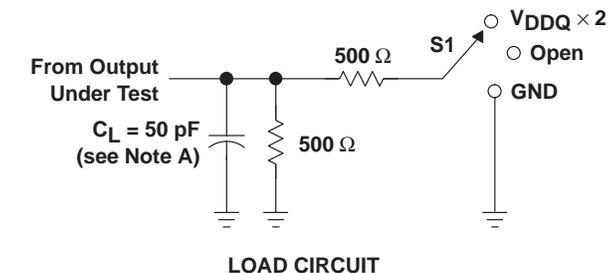
![Texas Instruments logo]

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 3.3 V ± 0.3 V AND V_{DDQ} = 2.5 ± 0.2 V

TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	$V_{DDQ} \times 2$
t_{PHZ}/t_{PZH}	GND

LOAD CIRCUIT

VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES

VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
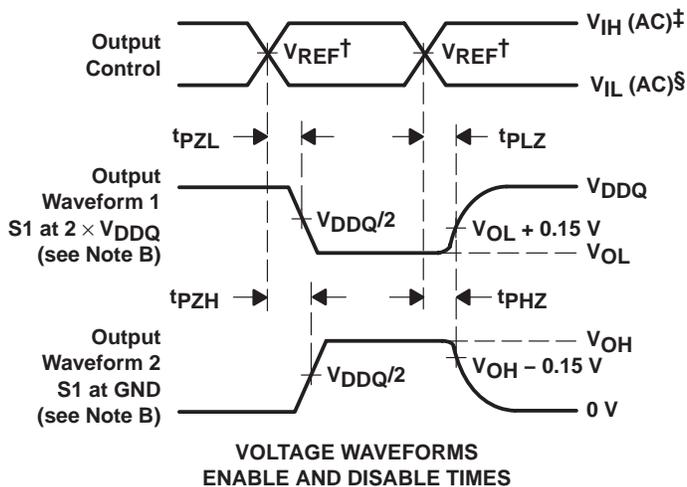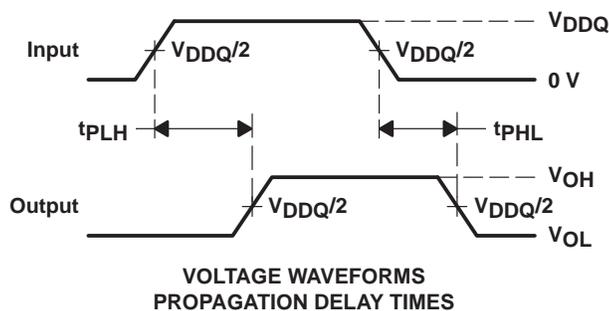
† V_{REF} = 0.38 × V_{CC}
‡ V_{IH}(AC) = V_{REF} + 350 mV
§ V_{IL}(AC) = V_{REF} − 350 mV

NOTES: A. C_L includes probe and jig capacitance.
　　　　 B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control.
　　　　　　 Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
　　　　 C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2 ns, t_f ≤ 2 ns.
　　　　 D. The outputs are measured one at a time with one transition per measurement.
　　　　 E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
　　　　 F. t_{PZL} and t_{PZH} are the same as t_{en}.
　　　　 G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
74CBTLV3857DBQRE4	ACTIVE	SSOP	DBQ	24		TBD	Call TI	Call TI	-40 to 85		Samples
74CBTLV3857DBQRG4	ACTIVE	SSOP	DBQ	24		TBD	Call TI	Call TI	-40 to 85		Samples
74CBTLV3857DWRE4	ACTIVE	SOIC	DW	24	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	CBTLV3857	Samples
74CBTLV3857DWRG4	ACTIVE	SOIC	DW	24	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	CBTLV3857	Samples
74CBTLV3857PWRE4	ACTIVE	TSSOP	PW	24	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	CL857	Samples
74CBTLV3857PWRG4	ACTIVE	TSSOP	PW	24	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	CL857	Samples
SN74CBTLV3857DWE4	ACTIVE	SOIC	DW	24		TBD	Call TI	Call TI	-40 to 85		Samples
SN74CBTLV3857DWG4	ACTIVE	SOIC	DW	24		TBD	Call TI	Call TI	-40 to 85		Samples
SN74CBTLV3857DWR	ACTIVE	SOIC	DW	24	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	CBTLV3857	Samples
SN74CBTLV3857PWR	ACTIVE	TSSOP	PW	24	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	CL857	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.
TBD: The Pb-Free/Green conversion plan has not been defined.
Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.
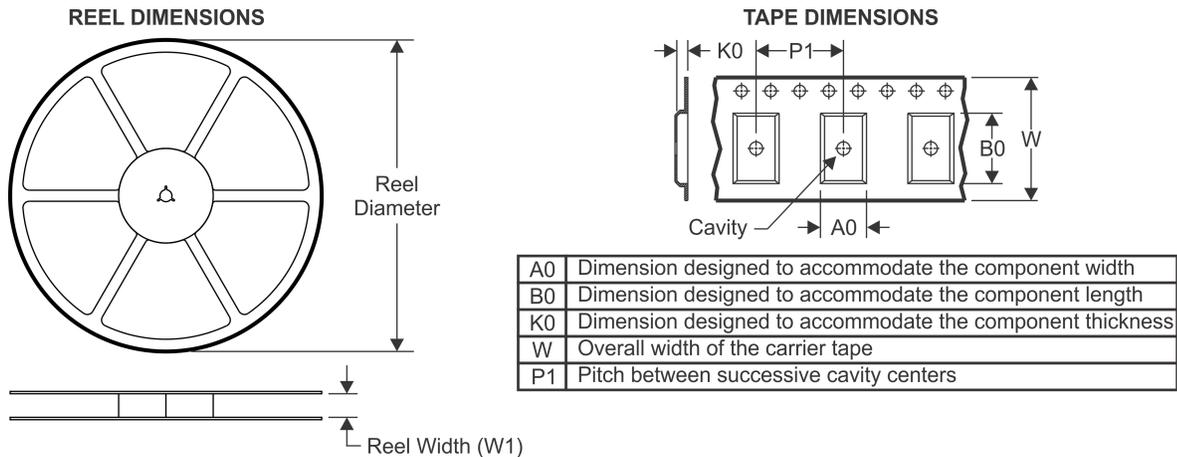**Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.
Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

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PACKAGE MATERIALS INFORMATION

TAPE AND REEL INFORMATION

REEL DIMENSIONS

TAPE DIMENSIONS

A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE

*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74CBTLV3857DWR	SOIC	DW	24	2000	330.0	24.4	10.75	15.7	2.7	12.0	24.0	Q1
SN74CBTLV3857PWR	TSSOP	PW	24	2000	330.0	16.4	6.95	8.3	1.6	8.0	16.0	Q1

TAPE AND REEL BOX DIMENSIONS
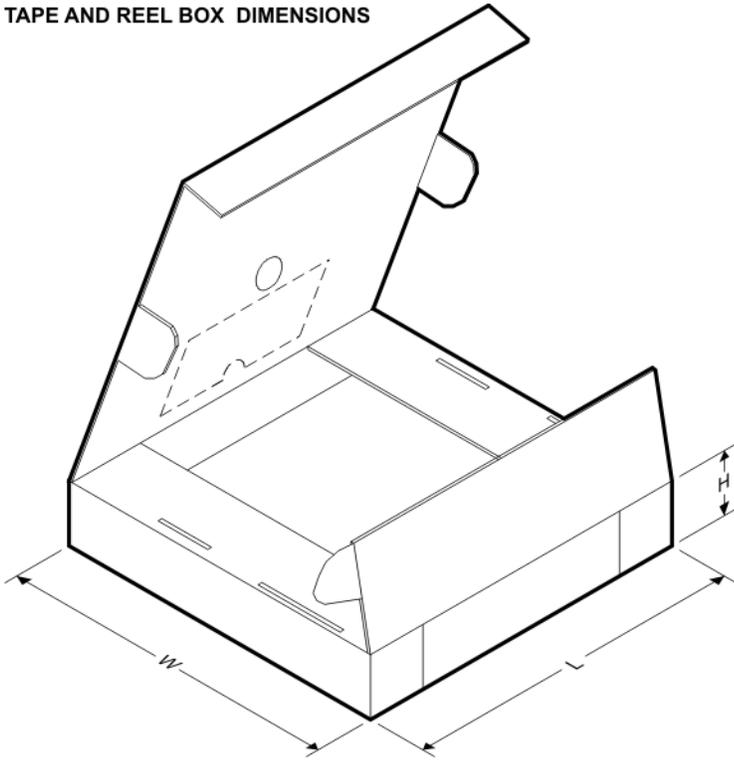
*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74CBTLV3857DWR	SOIC	DW	24	2000	367.0	367.0	45.0
SN74CBTLV3857PWR	TSSOP	PW	24	2000	367.0	367.0	38.0

DW (R−PDSO−G24)   PLASTIC SMALL OUTLINE

0.614 (15,60)
0.598 (15,20)

24   13

0.419 (10,63)
0.393 (9,97)

0.299 (7,60)
0.291 (7,40)

1   12

Pin 1
Index Area

0.050 (1,27)

0.020 (0,51)
0.012 (0,31)

⊕ 0.010 (0,25) Ⓜ

0.104 (2,65) Max

0.012 (0,30)
0.004 (0,10)

0.013 (0,33)
0.008 (0,20)

0.004 (0,10)

Gauge Plane

Seating Plane

0.010 (0,25)

0°–8°

0.050 (1,27)
0.016 (0,40)

4040000−5/G 01/11
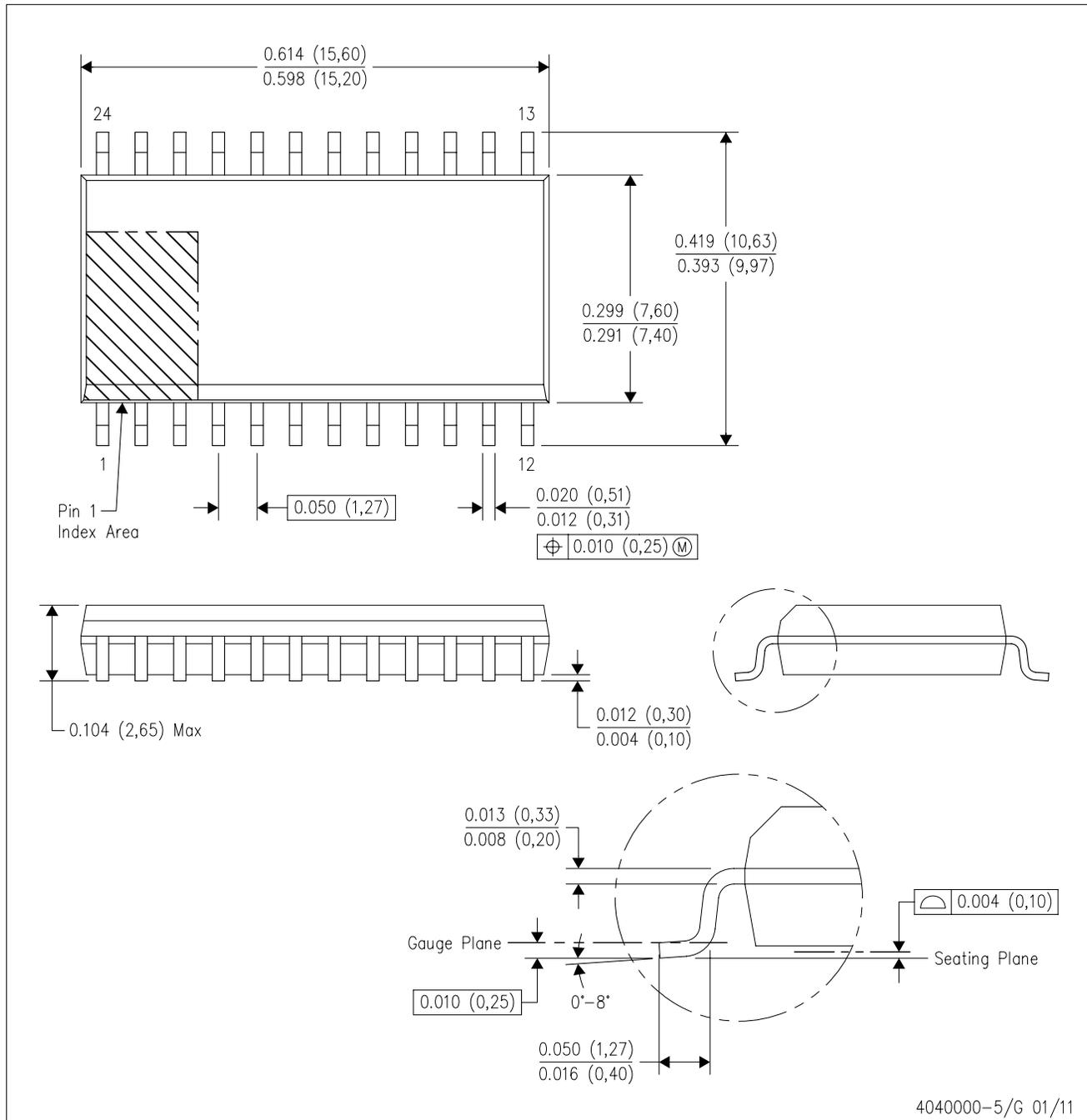
NOTES: A.   All linear dimensions are in inches (millimeters). Dimensioning and tolerancing per ASME Y14.5M−1994.
         B.   This drawing is subject to change without notice.
         C.   Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15).
         D.   Falls within JEDEC MS−013 variation AD.

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DBQ (R−PDSO−G24)   PLASTIC SMALL−OUTLINE PACKAGE
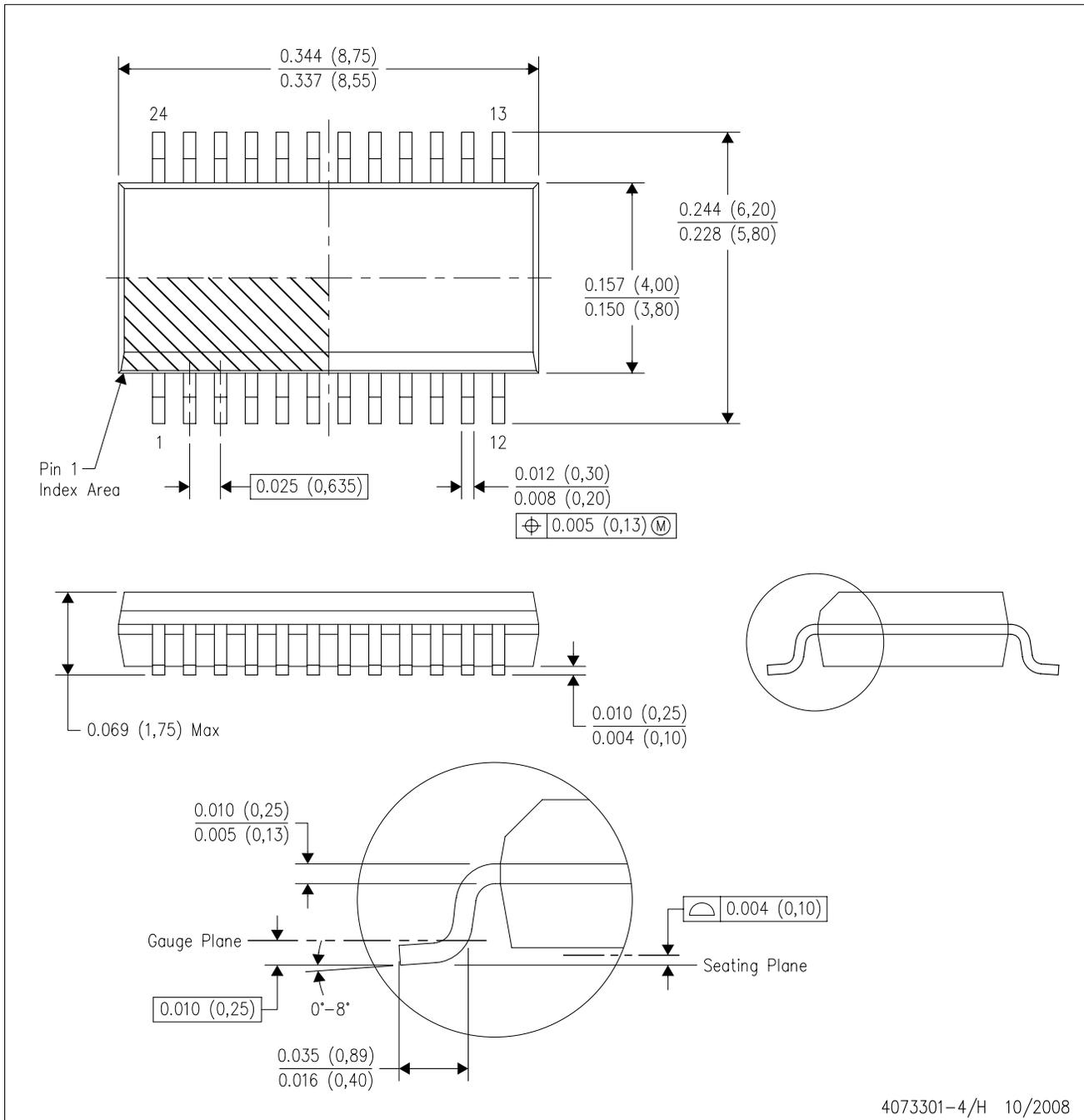
0.344 (8,75)
0.337 (8,55)

24   13

0.244 (6,20)
0.228 (5,80)

0.157 (4,00)
0.150 (3,80)

Pin 1
Index Area

1   12

0.025 (0,635)

0.012 (0,30)
0.008 (0,20)

⊕ 0.005 (0,13) Ⓜ

0.069 (1,75) Max

0.010 (0,25)
0.004 (0,10)

0.010 (0,25)
0.005 (0,13)

0.004 (0,10)

Gauge Plane

Seating Plane

0.010 (0,25)   0°−8°

0.035 (0,89)
0.016 (0,40)

4073301−4/H   10/2008

NOTES: A. All linear dimensions are in inches (millimeters).
        B. This drawing is subject to change without notice.
        C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15) per side.
        D. Falls within JEDEC MO−137 variation AE.

PW (R−PDSO−G24)   PLASTIC SMALL OUTLINE

0,65

0,30
0,19

⊕ 0,10 Ⓜ

24   13

Ⓓ 4,50   6,60
    4,30   6,20

1   12

7,90
7,70

Ⓒ

0,15 NOM

Gage Plane

0°−8°

0,25

0,75
0,50

1,20 MAX

0,15
0,05

Seating Plane

◁ 0,10
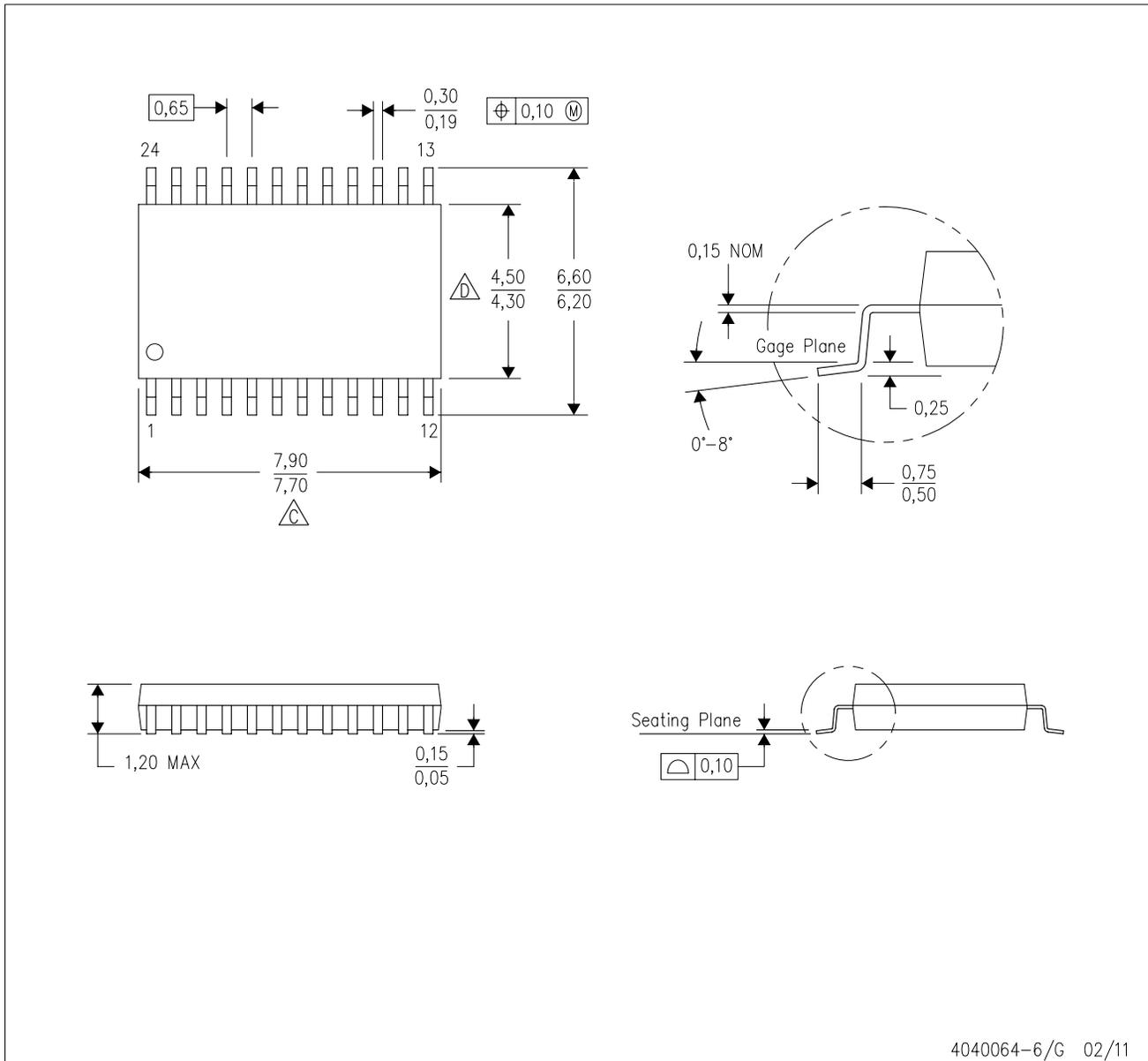
4040064−6/G 02/11

NOTES: A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M−1994.
         B. This drawing is subject to change without notice.
         Ⓒ Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall
             not exceed 0,15 each side.
         Ⓓ Body width does not include interlead flash. Interlead flash shall not exceed 0,25 each side.
         E. Falls within JEDEC MO−153

PW (R−PDSO−G24)   PLASTIC SMALL OUTLINE

Example Board Layout

Stencil Openings
Based on a stencil thickness
of .127mm (.005inch).

22x0,65

24x0,25

1,55

5,6

5,6

22x0,65

Example
Non Soldermask Defined Pad

Example
Solder Mask Opening
(See Note F)

0,3

1,6

Pad Geometry

0,07
All Around

4211284−4/F 12/12
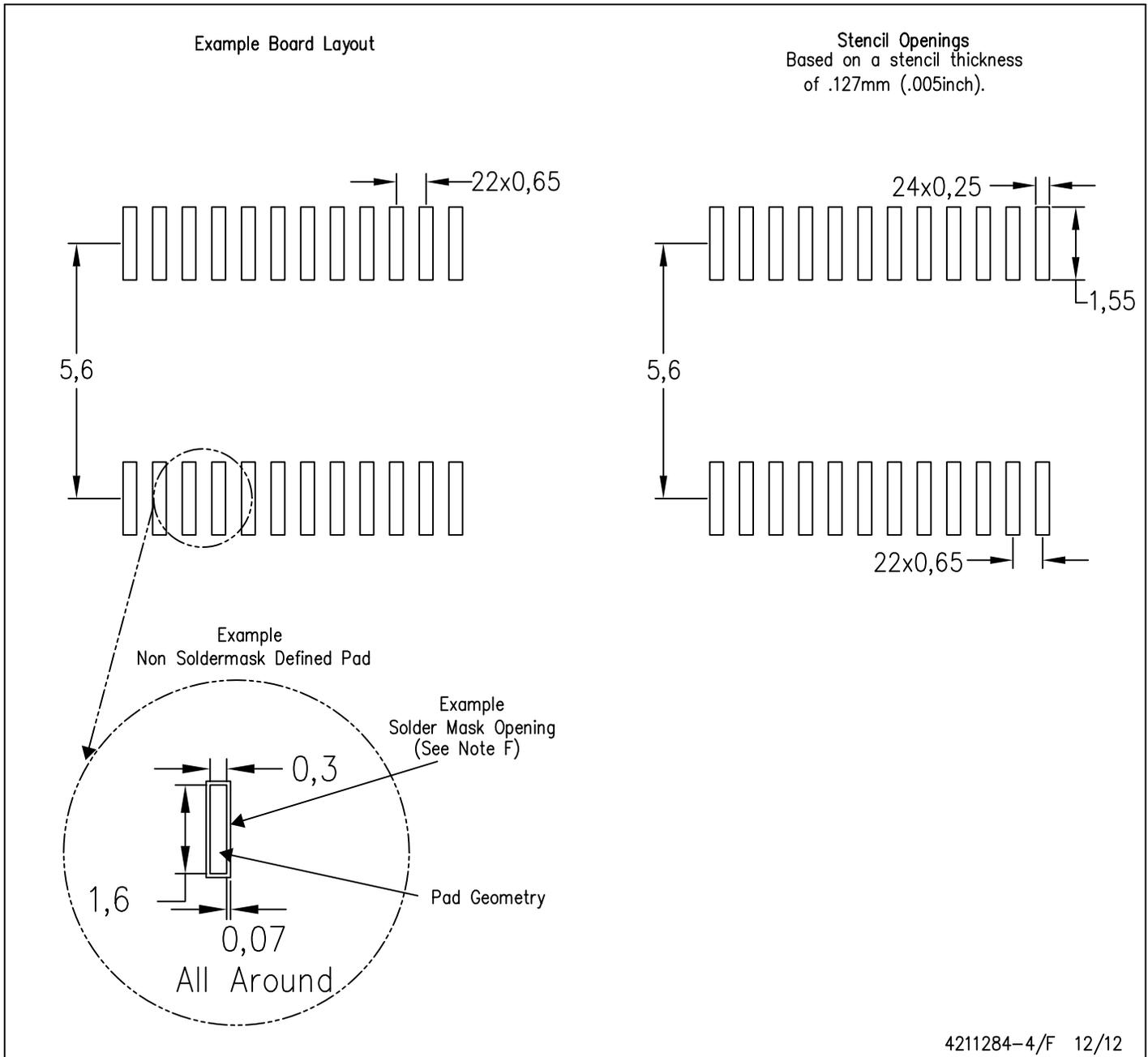
NOTES: A. All linear dimensions are in millimeters.
         B. This drawing is subject to change without notice.
         C. Publication IPC−7351 is recommended for alternate design.
         D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should
             contact their board assembly site for stencil design recommendations. Refer to IPC−7525 for other stencil recommendations.
         E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

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